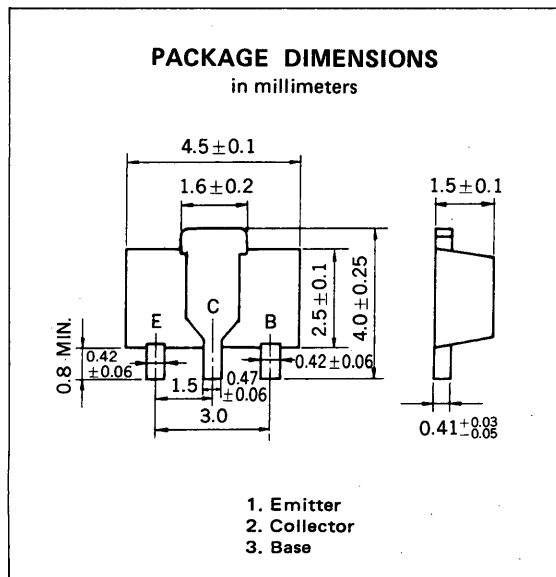


SILICON TRANSISTORS 2SB1115, 2SB1115A

PNP SILICON EPITAXIAL TRANSISTOR POWER MINI MOLD

DESCRIPTION

2SB1115, 2SB1115A are designed for audio frequency power amplifier and switching application, especially in Hybrid Integrated Circuits.



FEATURES

- World Standard Miniature Package
- Low $V_{CE(sat)} \cdot V_{CE(sat)} = -0.2$ V at 1 A
- Complement to 2SD1615, 2SD1615A

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

		2SB1115	2SB1115A	
Collector to Base Voltage	V_{CBO}	-60	-80	V
Collector to Emitter Voltage	V_{CEO}	-50	-60	V
Emitter to Base Voltage	V_{EBO}		-6	V
Collector Current (DC)	I_C		-1	A
Collector Current (Pulse)*	I_C		-2	A
Maximum Power Dissipation				
Total Power Dissipation at 25 °C Ambient Temperature**	P_T		2.0	W
Maximum Temperatures				
Junction Temperature	T_j		150	°C
Storage Temperature Range	T_{stg}		-55 to +150	°C

*PW ≤ 10 ms, Duty Cycle ≤ 50 %

**When mounted on ceramic substrate of 16 cm² x 0.7 mm

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

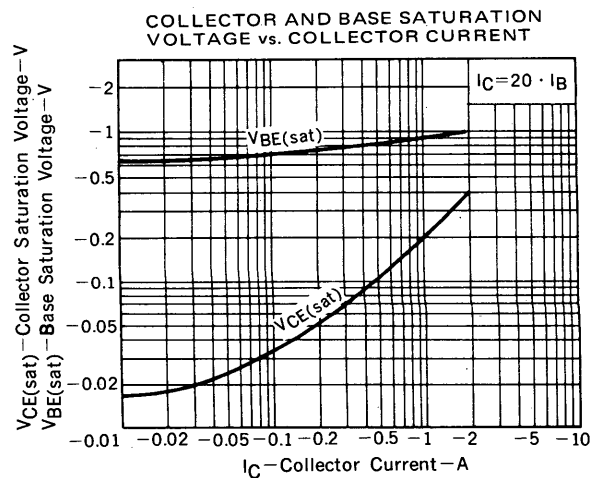
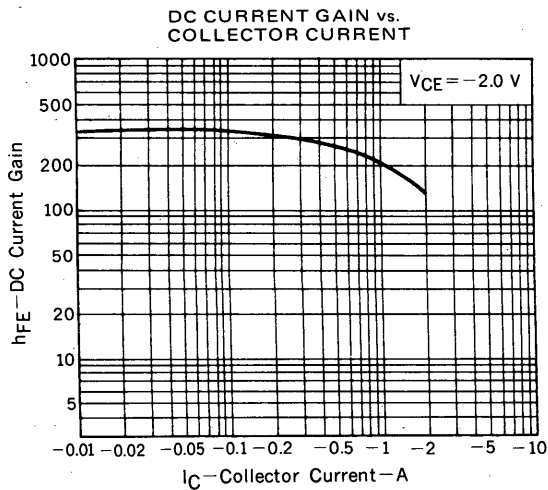
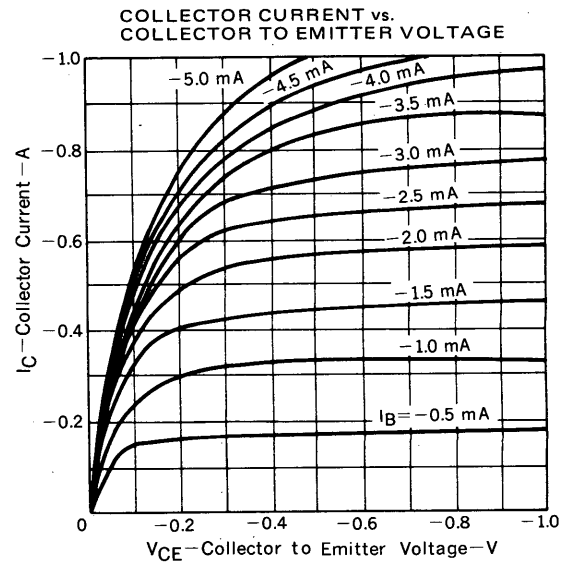
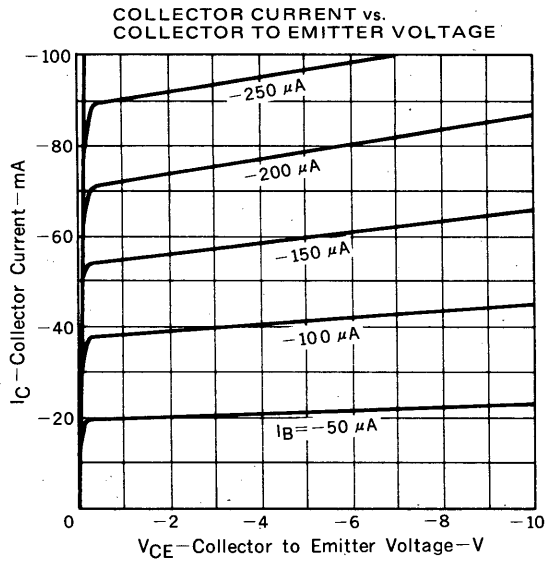
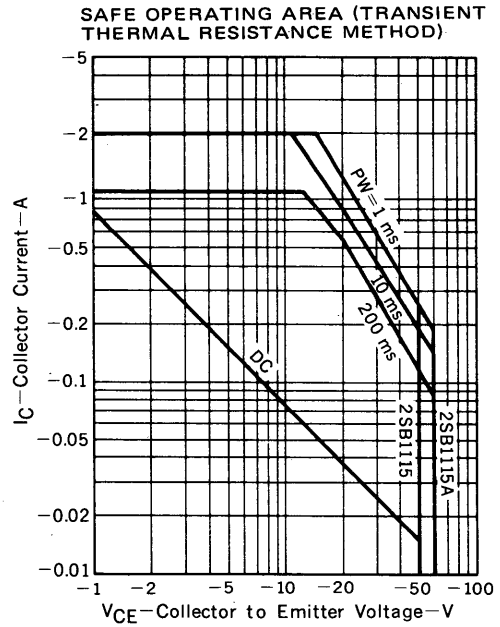
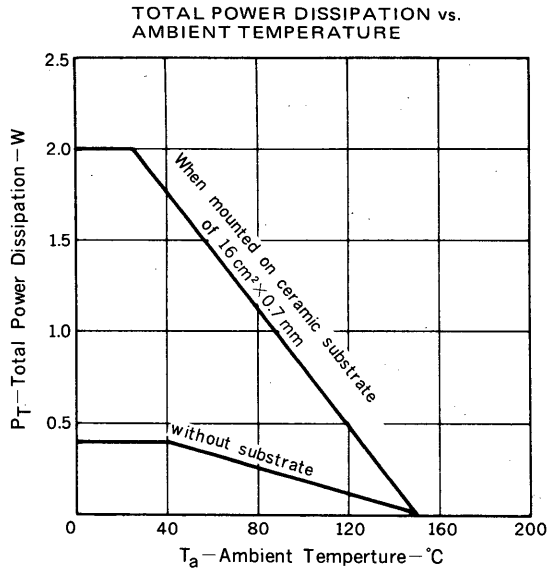
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Cutoff Current	I_{CBO}			-100	nA	2SB1115	$V_{CB} = -60$ V, $I_E = 0$
				-100	nA	2SB1115A	$V_{CB} = -80$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			-100	nA	$V_{EB} = -6.0$ V, $I_C = 0$	
DC Current Gain	h_{FE1} ***	135	340	600		2SB1115	$V_{CE} = -2.0$ V, $I_C = -100$ mA
		135	340	400		2SB1115A	
DC Current Gain	h_{FE2} ***	100	200			$V_{CE} = -2.0$ V, $I_C = -1.0$ A	
Collector Saturation Voltage	$V_{CE(sat)}$ ***		-0.2	-0.3	V	$I_C = -1.0$ A, $I_B = -50$ mA	
Base Saturation Voltage	$V_{BE(sat)}$ ***		-0.9	-1.2	V	$I_C = -1.0$ A, $I_B = -50$ mA	
Base to Emitter Voltage	V_{BE} ***	-600		-700	mV	$V_{CE} = -2.0$ V, $I_C = -50$ mA	
Gain Bandwidth Product	f_T	80	120		MHz	$V_{CE} = -2.0$ V, $I_E = -100$ mA	
Output Capacitance	C_{ob}		25		pF	$V_{CB} = -10$ V, $I_E = 0$, $f = 1.0$ MHz	

***Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2 %

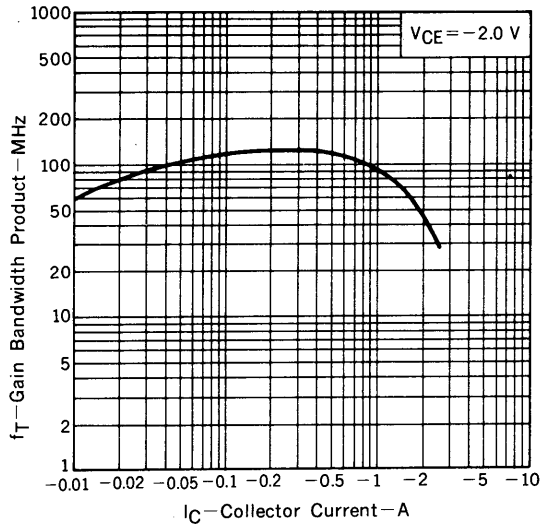
h_{FE} Classification

MARKING	2SB1115	YM	YL	YK
	2SB1115A	YQ	YP	
h_{FE}		135 to 270	200 to 400	300 to 600

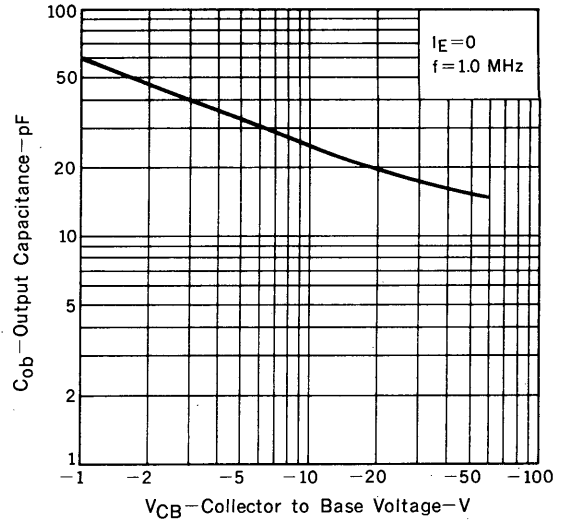
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



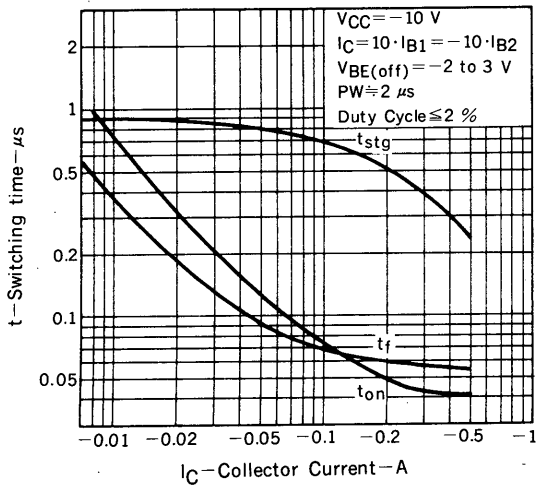
GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



SWITCHING TIME vs. COLLECTOR CURRENT



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

[MEMO]

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

The devices listed in this document are not suitable for use in aerospace equipment, submarine cables, nuclear reactor control systems and life support systems. If customers intend to use NEC devices for above applications or they intend to use "Standard" quality grade NEC devices for applications not intended by NEC, please contact our sales people in advance.

Application examples recommended by NEC Corporation

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.